



Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

Page 1 of 5

Application Number: 10/760,090

Filing Date: 01/15/2004

First Named Inventor: King

Art Unit: 2815

Examiner Name: ~~N/A~~ WOJCIECHOWICZ

Attorney Docket Number: PROG2000-1C3

Examiner Initials	Patent Number	Publication Date	Inventor Name
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Examiner
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Date

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Page 2 of 5

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

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Examiner
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Page 3 of 5

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Page 4 of 5

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Page 5 of 5

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